Battery Protection IC, OTP Function, 1-Cell Lithium-Ion Battery

LC05511XA, LC05512XA

Overview

LC05511XA/LC05512XA is a protection IC for 1 cell lithium-ion or lithium-polymer battery with built-in OTP. It provides highly accurate adjustable over-charge, over-discharge, over-current protection with adjustable detection delay by OTP. Current is detected by high precision external chip resistor. Which realizes accurate current detection over temperature.

Function

- Highly Accurate Detection Voltage/Current at $T_A = 25^{\circ}$ C, $V_{\rm CC}$ = 3.8 V
- Over-charge Detection Voltage: 4.1 V to 4.55 V (5 mV steps)
- Over-charge Release Hysteresis: 0 V, 0.1 V, 0.15 V, 0.2 V
- Over-discharge Detection Voltage: 2.0 V to 3.3 V (50 mV step)
- Over-discharge Release Hysteresis: 0 V to 0.075 V (25 mV step)
- Over-discharge Release Hysteresis2: 0 V, 0.2 V, 0.3 V, 0.4 V
- Discharge Over-current Detection Voltage1: 3 mV to 30 mV (0.3 mV step)
- Discharge Over-current Detection Voltage2: 3 mV to 30 mV (0.6 mV step)
- Short Current Detection Voltage: 20 mV to 70 mV (5 mV step)
- Charge Over-current Detection Voltage: -30 mV to -3 mV (-0.6 mV step)
- Over-charge Detection Delay Time: 512 ms, 1024 ms, 2048 ms, 4096 ms
- Over-discharge Detection Delay Time: 32 ms, 64 ms, 128 ms, 256 ms
- Discharge Over-current Detection Delay Time1: 32 ms, 64 ms, 128 ms, 256 ms, 512 ms, 1024 ms, 2048 ms, 3482 ms
- Discharge Over-current Detection Delay Time2: 4 ms, 8 ms, 16 ms, 32 ms
- Short-current Detection Delay Time: 250 μs, 450 μs
- Charge Over-current Detection Delay Time: 4 ms, 8 ms, 16 ms, 128 ms
- 0 V Battery Charging: "Permission (LC05511XA)", "Inhibit (LC05512XA)"
- Auto Wake-up Function: "Permission (LC05511XA)", "Inhibit (LC05512XA)"

Typical Applications

- Smart Phone
- Tablet
- Wearable Device



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0.85 x 1.17 x 0.40 CASE 567TL

PART MARKING

1x0v **ALYW**

1x0y = Specific Device Code

x = 1 or 2

y = 1, 2, 3 or 4

= Assembly Location

= Wafer Lot

= Year

W = Work Week

ORDERING INFORMATION

Device	Package	Shipping [†]			
LC05511Z01XATBG					
LC05511Z02XATBG					
LC05511Z03XATBG	WLCSP6	5000 /			
LC05511Z04XATBG	(Pb-Free)	Tape & Reel			
LC05512Z01XATBG					
LC05512Z02XATBG					

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

SPECIFICATIONS

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Conditions	Ratings	Unit
Supply Voltage	VCC		-0.3 to 12.0	V
CS Terminal Input Voltage	VCS		-0.3 to 7	V
VM Terminal Input Voltage	VVM		VCC - 24.0 to VCC + 0.3	V
CO Terminal Voltage	VCO		VCC - 24.0 to VCC + 0.3	V
DO Terminal Voltage	VDO		-0.3 to 7	V
Storage Temperature	T _{stg}		-55 to +125	°C
Operating Ambient Temperature	T _{opr}		-40 to +85	°C
Allowable Power Dissipation	P _d	Glass epoxy two-layer board. Board size 42 mm × 30 mm × 1.6 mm	0.55	W
Junction Temperature	Tj		125	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

EXAMPLE OF APPLICATION CIRCUIT

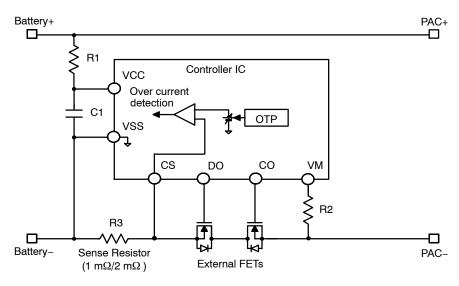


Figure 1. Example of Application Circuit

Components	Min	Recommended Value	Max	unit Description		
R1	0.68	1	1.2	.2 k Ω Battery+ is filtered to VCC by R1 and		
R2	0.1	1	2	k Ω Protection from reverse connection of charge		
C1	0.01	0.1	1.0	μF	Battery+ is filtered to VCC by R1 and C1	
R3	1		20	mΩ	Sense resistor for over-current detection	

ELECTRICAL CHARACTERISTICS (R1 = 1 k Ω , R2 = 1 k Ω , VCC = 3.8 V (Note 1))

Parameter	Symbol	Condition	ons	Min	Тур	Max	Unit	TEST Circui
DETECTION VOLTAGE								
Over-charge Detection	Vov	R1 = 1 kΩ	T _A = 25°C	Vov_set - 15	Vov_set	Vov_set + 15	mV	В
Voltage			T _A = -20 to 60°C	Vov_set - 20	Vov_set	Vov_set + 20		
Over-charge Release	Vovr1	R1 = 1 kΩ	T _A = 25°C	Vovr_set - 30	Vovr_set	Vovr_set + 30	mV	В
Voltage		VM < Vcocr & CS = 0	T _A = -20 to 60°C	Vovr_set - 55	Vovr_set	Vovr_set + 40		
	Vovr2	R1 = 1 kΩ VM > Vcocr & CS = 0	T _A = 25°C	Vov_set - 20	Vov_set	Vov_set + 15	mV	I
		VIVI > VCCCI & CG = 0	T _A = -20 to 60°C	Vov_set - 25	Vov_set	Vov_set + 20		
Over-discharge Detection Voltage	Vuv	R1 = 1 kΩ	T _A = 25°C	Vuv_set - 35	Vuv_set	Vuv_set + 35	mV	В
vollago			$T_A = -20 \text{ to } 60^{\circ}\text{C}$	Vuv_set - 55	Vuv_set	Vuv_set + 55		
Over-discharge Release Voltage1	Vuvr1	R1 = 1 kΩ VM = 0 V	T _A = 25°C	Vuvr1_set - 50	Vuvr1_set	Vuvr1_set + 50	mV	В
vollago		VW = 0 V	$T_A = -20 \text{ to } 60^{\circ}\text{C}$	Vuvr1_set - 80	Vuvr1_set	Vuvr1_set + 80		
Over-discharge Release Voltage2	Vuvr2	R1 = 1 k Ω VM = Open	T _A = 25°C	Vuvr2_set - 100	Vuvr2_set	Vuvr2_set + 100	mV	D
vollago_		VIII = Open	$T_A = -20 \text{ to } 60^{\circ}\text{C}$	Vuvr2_set - 110	Vuvr2_set	Vuvr2_set + 110		
Discharge Over-current Detection Voltage	Vdoc1	R2 = 1 kΩ	T _A = 25°C	Vdoc1 - 0.9	Vdoc1_set	Vdoc1 + 0.9	mV	F
(Primary Protection)			$T_A = -20 \text{ to } 60^{\circ}\text{C}$	Vdoc1 - 1.0	Vdoc1_set	Vdoc1 + 1.0		
Discharge Over-current Detection Voltage2	Vdoc2	R2 = 1 kΩ	T _A = 25°C	Vdoc1 - 1.8	Vdoc2_set	Vdoc1 + 1.8	mV	F
(Secondary Protection)			T _A = -20 to 60°C	Vdoc1 - 2.0	Vdoc2_set	Vdoc1 + 2.0		
Discharge Over-current Detection Voltage	Vshrt	R2 = 1 kΩ	T _A = 25°C	Vshrt_set - 5	Vshrt_set	Vshrt_set + 5	mV	F
(Short circuit)			Ta = −20 to 60°C	Vshrt_set - 6	Vshrt_set	Vshrt_set + 6		
Discharge Over-current (Short) Release Voltage			T _A = 25°C	VCC - 1.1	VCC - 0.65	VCC - 0.2	V	Α
		R2 = 1 kΩ	T _A = -20 to 60°C	VCC - 1.2	VCC - 0.65	VCC - 0.1		
Charge Over-current Detection Voltage			T _A = 25°C	Vcoc_set - 1.8	Vcoc_set	Vcoc_set + 1.8	mV	F
			T _A = -20 to 60°C	Vcoc_set - 2.0	Vcoc_set	Vcoc_set + 2.0		
Charge Over-current Release Voltage	Vcocr	R2 = 1 kΩ CS = 0 V	T _A = 25°C	0.08	0.2	0.32	V	Α
			T _A = -20 to 60°C	0.05	0.2	0.35		
INPUT VOLTAGE								
0 V Battery Charge Permission Charger Voltage (LC05511XA)	Vchg	VCC - VM VCC = VSS = 0 V	25°C			1.4	V	А
0 V Battery Charging Inhibition Battery Voltage (LC05512XA)	Vinh	VM = −2 V		0.85	1.0	1.15		
CURRENT CONSUMP	TION	•		•		•		
Operating Current	Icc	At normal state	25°C VCC = 3.8 V		3	6	μА	J
Stand-by Current (LC05511XA)	Istb	At Stand-by state Auto wake-up = enable	25°C VCC = 2.0 V			0.95	μΑ	J
Shutdown Current (LC05512XA)	Ishut	At Shutdown state				0.1		
RESISTANCE								_
Internal Resistance (VCC-VM)	Rvmu	VCC = 2.0 V VM = 0 V	25°C	150	300	600	kΩ	E
Internal Resistance (VSS-VM)	Rvmd	VCC = 3.8 V VM = 0.1 V	25°C	5	10	20	kΩ	E
CO Output Resistance (High)	Rcoh	VCC = 3.8 V CO = 3.3 V CS = 0 V	25°C	6	12	24	kΩ	Н
CO Output Resistance (Low)	Rcol	VCC = 4.5 V CO = 0.5 V CS = 0 V	25°C	0.35	0.7	1.4	kΩ	Н
DO Output Resistance (High)	Rdoh	VCC = 3.8 V DO = 3.3 V CS = 0 V	25°C	0.8	1.6	3.2	kΩ	G

ELECTRICAL CHARACTERISTICS (R1 = 1 k Ω , R2 = 1 k Ω , VCC = 3.8 V (Note 1))

Parameter	Symbol	Conditi	ons	Min	Тур	Max	Unit	TEST Circuit
RESISTANCE								
DO Output Resistance (Low)	Rdol	VCC = 2.0 V CS = 0 V DO = 0.5 V	25°C	0.1	0.3	0.6	kΩ	G
DETECTION AND REL	EASE DE	LAY TIME						
Over-charge Detection Delay Time	Tov	VCC = Vovr1_min to Vov_max	25°C	Tov_set × 0.8	Tov_set	Tov_set × 1.2	ms	В
Delay Time		VM = CS = 0 V	T _A = -20 to 60°C	Tov_set × 0.7	Tov_set	Tov_set × 1.3		
Over-charge Release Delay Time	Tovr	VCC = Vov_max to Vovr1_min	25°C	12.8	16	19.2	ms	В
Delay Time		VM = CS = 0 V	T _A = -20 to 60°C	11.2	16	20.8		
Over-discharge Detection Delay Time	Tuv	VCC = Vuvr1_max to Vuv_min	25°C	Tuv_set × 0.8	Tuv_set	Tuv_set × 1.2	ms	В
Delay Time		VM = CS = 0 V	$T_A = -20 \text{ to } 60^{\circ}\text{C}$	Tuv_set × 0.65	Tuv_set	Tuv_set × 1.35		
Over-discharge Release Delay Time	Tuvr	VCC = Vuv_min to Vuvr1 max	25°C	0.84	1.05	1.26	ms	В
Delay Time		VM = CS = 0 V	$T_A = -20 \text{ to } 60^{\circ}\text{C}$	0.68	1.05	1.42		
Discharge Over-current Detection Delay Time 1	Tdoc1	CS = 0 V to Vdoc1 max	25°C	Tdoc1_set × 0.8	Tdoc1_set	Tdoc1_set × 1.2	ms	F
Detection Delay Time 1		VM = 0 V	T _A = -20 to 60°C	Tdoc1_set × 0.7	Tdoc1_set	Tdoc1*_set×1.3		
Discharge Over-current Detection Delay Time 2	Tdoc2	VM = 0 V to Vdoc2 max	25°C	Tdoc2_set × 0.8	Tdoc2_set	Tdoc2_set × 1.2	ms	F
Detection Delay Time 2		VM = 0 V	T _A = -20 to 60°C	Tdoc2_set × 0.7	Tdoc2_set	Tdoc2_set × 1.3		
Discharge Over-current Release Delay Time	Tdocr	VM = 3.8 V to 2.7 V CS = 0 V	25°C	3.2	4	4.8	ms	Α
Helease Delay Time		03 = 0 V	T _A = -20 to 60°C	2.8	4	5.2		
Short-current Detection Delay Time	Tshrt	CS = 0 V to Vshrt_max VM = 0 V	25°C	Tshrt_set × 0.7	Tshrt_set	Tshrt_set × 1.3	μs	F
Detection Delay Time		VIVI = U V	$T_A = -20 \text{ to } 60^{\circ}\text{C}$	Tshrt_set × 0.6	Tshrt_set	Tshrt_set × 1.4		
Charge Over-current	Tcoc	CS = 0 V to Vcoc_min VM = 0 V	25°C	Tcoc_set × 0.8	Tcoc_set	Tcoc_set × 1.2	ms	F
Detection Delay Time		V IVI = U V	T _A = -20 to 60°C	Tcoc_set × 0.7	Tcoc_set	Tcoc_set × 1.3		
Charge Over-current Release Delay Time	Tcocr	VM = 0 V to Vcocr max	25°C	3.2	4	4.8	ms	F
Holoade Delay Hille		CS = 0 V	T _A = -20 to 60°C	2.8	4	5.2		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. The specification in high temperature and low temperature are guaranteed by design.

TEST CIRCUITS

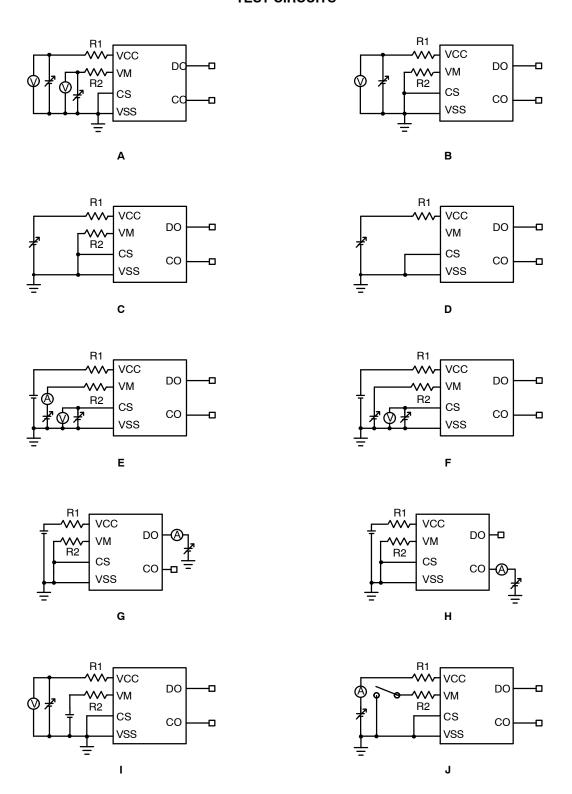


Figure 2. Test Circuits

Table 1. ADJUSTABLE PARAMETERS

Parameter	Unit	Range	Typical Value Setting Guide
Vov	mV	4100~4550	5 mV step
Vovr	mV	Vov – Vovr_Hy	Vovr_Hy: 0, 100, 150, 200 (4 steps)
Vuv	mV	2000~3300	50 mV step
Vuvr1	mV	Vuv + Vuvr1_Hy	Vuvr1_Hy: 0, 25, 50, 75 (4 steps)
Vuvr2	mV	Vuv + Vuvr2_Hy	Vuvr2_Hy: 0, 200, 300, 400 (4 steps)
Vdoc1	mV	3 to 30	0.3 mV step
Vdoc2	mV	3 to 30	0.6 mV step
Vshrt	mV	20 to 70	5 mV step
Vcoc	mV	−30 to −3	0.6 mV step

Parameter	Unit	Typical Value Setting Guide
Tov	ms	512, 1024, 2048, 4096
Tuv	ms	32, 64, 128, 256
Tdoc1	ms	32, 64, 128, 256, 512, 1024, 2048, 3482
Tdoc2	ms	4, 8, 16, 32
Tshrt	μs	250, 450
Tcoc	ms	4, 8, 16, 128

Table 2. SELECTION GUIDE

Device	Vov (mV)	Vovr1 (mV)	Vovr2 (mV)	Vuv (mV)	Vuvr1 (mV)	Vuvr2 (mV)	Vdoc1 (mV)	Vdoc2 (mV)	Vshrt (mV)	Vcoc (mV)	Tov (ms)	Tuv (ms)	Tdoc1 (ms)	Tdoc2 (ms)	Tshrt (μs)	Tcoc (ms)
LC05511Z01XATBG	4475	4325	4475	2500	2500	2900	14.0	20.0	50.0	-14.0	1024	64	3482	16	250	16
LC05511Z02XATBG	4530	4380	4530	2350	2350	2550	14.0	20.0	50.0	-20.0	1024	64	3482	16	250	16
LC05511Z03XATBG	4475	4325	4475	2500	2500	2900	7.5	10.0	25.0	-10.0	1024	64	3482	16	250	16
LC05511Z04XATBG	4530	4380	4530	2350	2350	2550	7.5	10.0	25.0	-12.5	1024	64	3482	16	250	16
LC05512Z01XATBG	4475	4325	4475	2300	2300	-	15	20.0	30	-13.0	1024	64	32	8	250	16
LC05512Z02XATBG	4100	4100	4100	2500	2500	-	9	13	70	-30	2048	256	3482	32	450	128

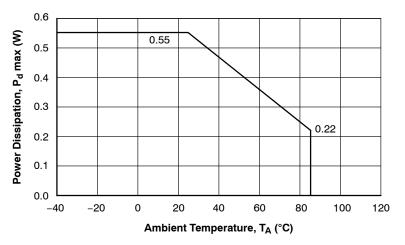


Figure 3. P_d max-T_A Graph

Table 3. PIN FUNCTION

Pin No.	Symbol	Pin Function
A1	VSS	VSS terminal
A2	VCC	VCC terminal
A3	CS	Over-current detection input terminal
B1	DO	Discharge FET control terminal
B2	CO	Charge FET control terminal
B3	VM	Charger negative voltage input terminal

BLOCK DIAGRAM

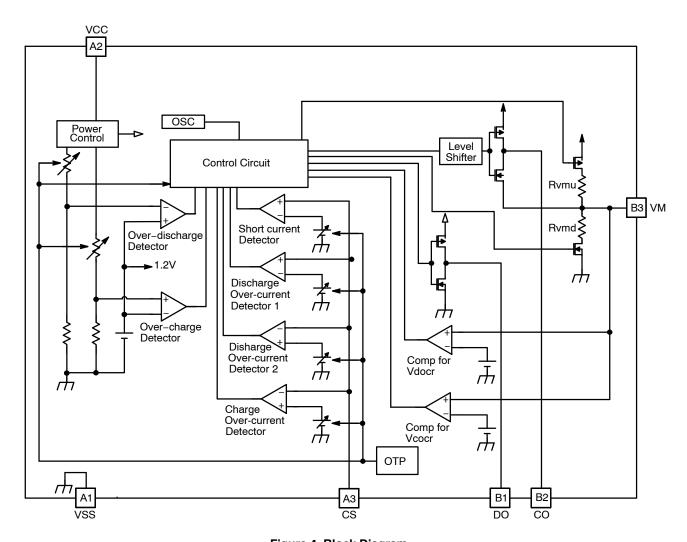


Figure 4. Block Diagram

DESCRIPTION OF OPERATION

The battery voltage is detected between VCC pin and VSS pin and the battery current is detected between VSS pin and CS pin.

(1) Normal State

 "VCC voltage" is between "over-discharge detection voltage (Vuv)", "over-charge detection voltage (Vov)", and "CS voltage" is between "charge over-current detection voltage (Vcoc)", "discharge over-current detection voltage (Vdoc)", and "VM voltage" is lower than "dicharge over-current (short) release voltage (Vdocr)".

This is the normal state. Both CO and DO are high level output. Charge and discharge is allowed.

(2) Over-charging State

 "VCC voltage" is higher than or equal to "over-charge detection voltage (Vov)" for longer than "over-charge detection delay time (Tov)".

This is the over charging state. CO is low level output.

This is the over-charging state, CO is low level output. Charge is prohibited.

- Release from Over-charging State 1
 - "VM voltage" is lower than "charge over-current (short) release voltage (Vcocr)". Then "VCC voltage" is lower than "over-charge release voltage1 (Vovr1)" for longer than "over-charging release delay time (Tovr)".
- Release from Over-charging State 2
 "VM voltage" is higher than "charge over-current (short) release voltage (Vcocr)". Then "VCC voltage" is lower than "over-charge release voltage2 (Vovr2) for longer than "over-charge release delay time (Tovr)".

(3) Over-discharging State

• "VCC voltage" is lower than "over-discharge detection voltage (Vuv)" for longer than "over-discharge delay time (Tuv)".

This is the over-discharging state, DO is low level output. Discharge is prohibited.

During over-discharging state, VM pin is pulled up to Vcc by internal resistor (Rvmu) and circuits are shut down. The low power consumption is kept.

- Release from Over-discharging State 1
 Charger is connected, then "VCC voltage" goes higher than "over-discharge release voltage1 (Vuvr1)" for longer than "over-discharge release delay time (Tuvr)".
- Release from Over-discharging State
 (with Auto Wake-up Feature) 2 (LC05511XA)
 "VCC voltage" is higher than "over-discharge release
 voltage2 (Vuvr1)" without charger for longer than
 "over-discharge release delay time (Tuvr)".

(4) Discharging Over-current State

- <u>Discharge Over-current Detection 1</u>
 CS terminal is higher than or equal to "discharge over-current detection voltage (Vdoc1)" for longer than "discharge over-current detection delay time (Tdoc1)".
 DO is low level output. Discharge is prohibited.
- <u>Discharge Over-current Detection 2</u>
 CS terminal is higher than or equal to "discharge over-current detection voltage2 (Vdoc2)" for longer than "discharge over-current detection delay time 2 (Tdoc2)".

DO is low level output. Discharge is prohibited.

- Discharge Over-current Detection (Short Circuit)
 CS terminal is higher than or equal to "discharge over-current detection voltage (Short circuit) (Vshrt)" for longer than "short-current detection delay time (Tshrt)".
 - DO is low level output. Dischaege is prohibited. During discharging over-current state, VM pin is pulled down to Vss by internal resistor (Rvmd).
- Release from Discharging Over-current State
 "CS voltage" goes lower than "discharge over-current detection voltage (Vdoc1)" and VM voltage goes lower than "discharge over-current (short) release voltage (Vdocr)" for longer than "discharge over-current release delay time (Tdocr)".

(5) Charging Over-current State

- "CS voltage" goes lower than or equal to "charge over-current detection voltage (Vcoc) for longer than "charge over-current detection delay time (Tcoc)". This is the charging over-current state, CO is low level output. Charge is prohibited.
- Release from charging over-current state

 "CS voltage" goes lower than "charge over-current detection voltage (Vcoc)" and "VM voltage" goes lower than "charge over-current release voltage (Vcocr)" for longer than "charge over-current release delay time (Tcocr)".

(6) 0 V Battery Charging (LC05511XA)

• When the Battery voltage is lower than or equal to "0 V battery charge permission voltage (Vchg)", charge is allowed if charger voltage is higher than or equal "0 V battery charge permission voltage (Vchg)". CO is fixed by the "VCC voltage".

(7) 0 V Battery Protection Function (LC05512XA)

• This function protects the battery when a short circuit in the battery (0 V battery) is detected, at which point charging will be prohibited.

When the voltage of a battery is below "0 V battery charging inhibition battery voltage (Vinh)", CO is low level output. Charge is prohibited.

TIMING CHARTS

Over Charge Voltage and Charge Over Current

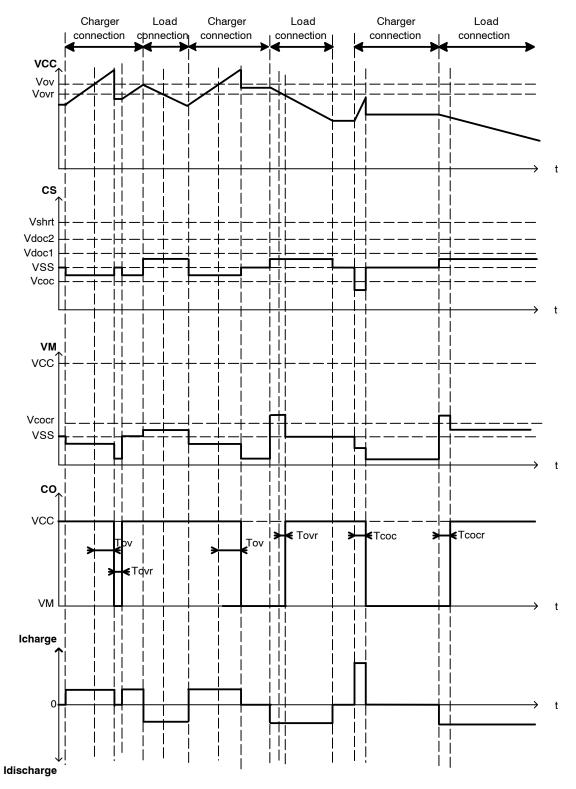
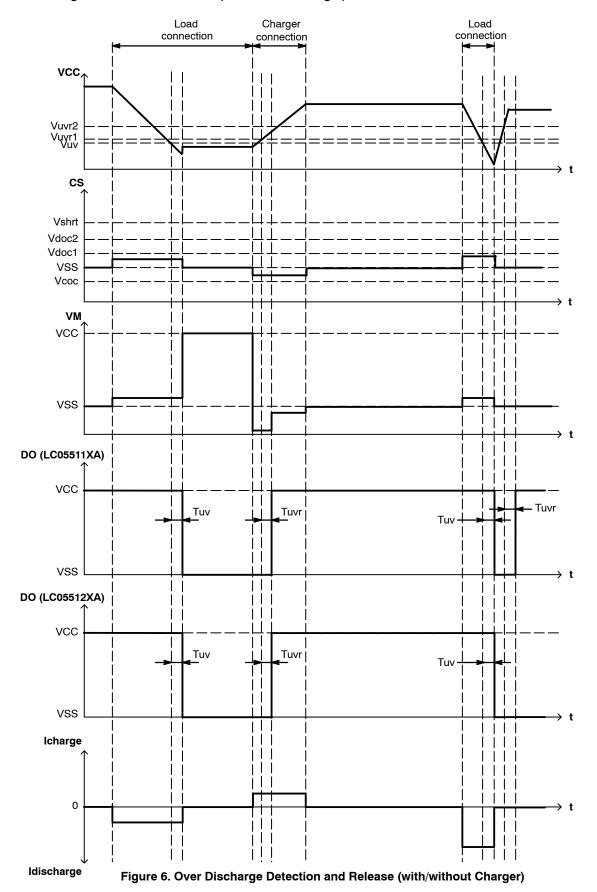


Figure 5. Over Charge Voltage and Charge Over Current

Over Discharge Detection and Release (with/without Charger)



Discharge Over Current and Short Current Detection and Release

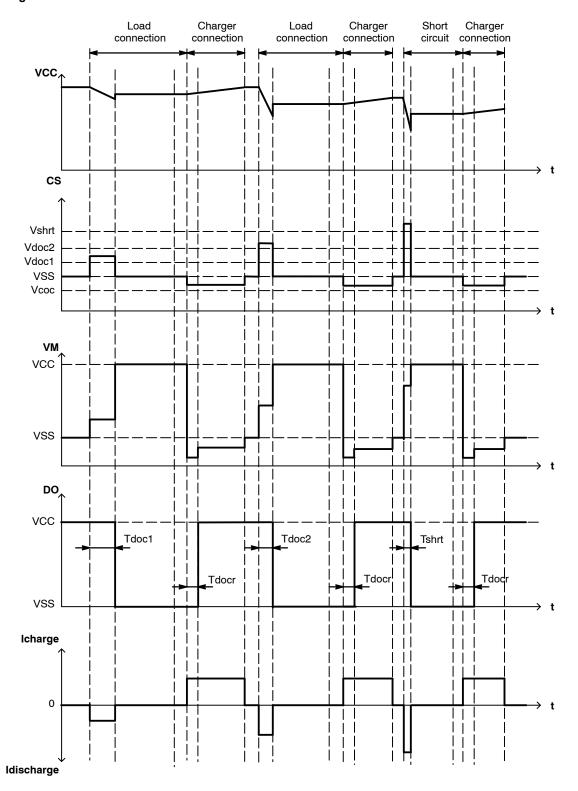


Figure 7. Discharge Over Current and Short Current Detection and Release

CHARACTERISTICS OF LC05511Z04XA (TYPICAL DATA)

(1) Current Consumption and Protection Detection Voltage

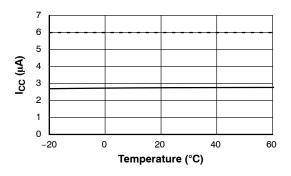


Figure 8. I_{CC} vs. Temperature

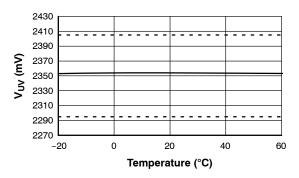


Figure 10. V_{UV} vs. Temperature

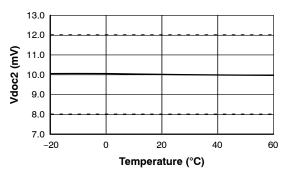


Figure 12. Vdoc2 vs. Temperature

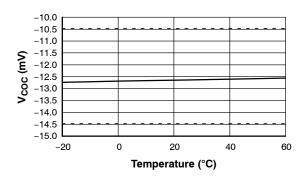


Figure 14. V_{COC} vs. Temperature

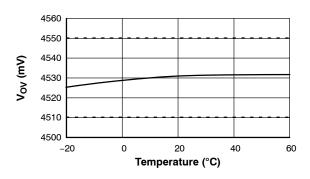


Figure 9. V_{OV} vs. Temperature

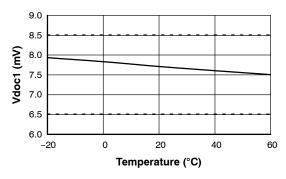


Figure 11. Vdoc1 vs. Temperature

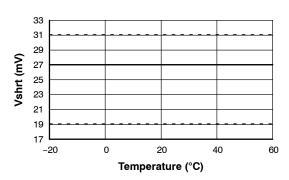


Figure 13. Vshrt vs. Temperature

CHARACTERISTICS OF LC05511Z04XA (TYPICAL DATA)

(2) Protection Detection Delay Time

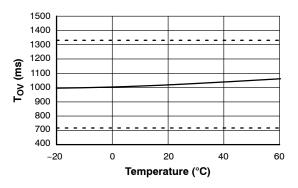
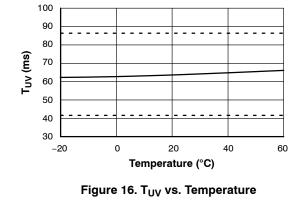


Figure 15. T_{OV} vs. Temperature



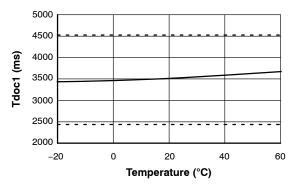


Figure 17. Tdoc1 vs. Temperature

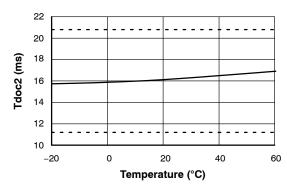


Figure 18. Tdoc2 vs. Temperature

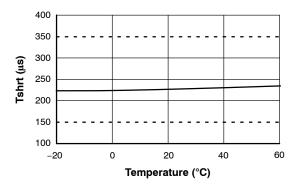


Figure 19. Tshrt vs. Temperature

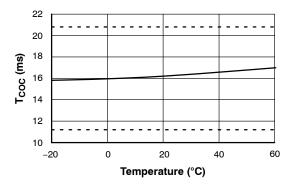
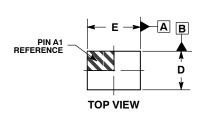


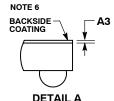
Figure 20. T_{COC} vs. Temperature

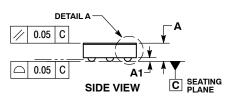


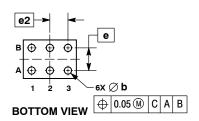
WLCSP6 0.85x1.17x0.40 CASE 567TL ISSUE O

DATE 14 MAR 2017









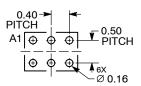
DETAIL A OPTIONAL CONSTRUCTION

NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 1 14.3M, 1994.
 2 CONTROLLING DIMENSION: MILLIMETERS.
 3. DATUM C, THE SEATING PLANE, IS DEFINED BY THE SPHERICAL CROWNS OF THE CONTACT BALLS
- 4. COPLANARITY APPLIES TO THE SPHERICAL
- CROWNS OF THE SOLDER BALLS.
 DIMENSION 6 IS MEASURED AT THE MAXIMUM
- CONTACT BALL DIAMETER PARALLEL TO DATUM C.
 6. BACKSIDE COATING IS OPTIONAL.

	MILLIMETERS							
DIM	MIN NOM MAX							
Α			0.40					
A1	0.05	0.08	0.11					
АЗ	(0.025 REF						
b	0.11	0.16	0.21					
D	0.80	0.85	0.90					
E	1.12	1.12 1.17 1.22						
е	0.50 BSC							
e2		0.40 BSC	;					

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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